

1-Line Bi-directional Low Capacitance TVS Diode

Description

The PESDU0561P1L is bi-directional TVS diode, provide fast response time, very low capacitance and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The PESDU0561P1L complies with the IEC 61000-4-2 (ESD) standard with ±15kV air and ±8kV contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead- free DFN package. The small size and very low capacitance make PESDU0561P1L an ideal choice to protect cellphone, digital cameras, audio players, data interface and many other portable applications.

Features

Ultrasmall package: 1.0x0.6x0.5mm

Protects one data or power line

Very low capacitance: 2.5pF typical

Ultralow leakage: nA level

• Low operating voltage: 5V

Low clamping voltage

• 2-pin leadless package

Complies with following standards:

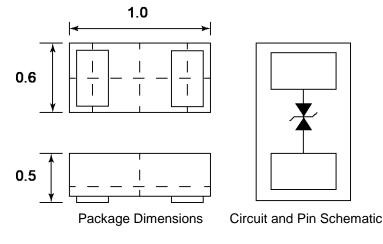
- IEC 61000-4-2 (ESD) immunity test

Air discharge: ±15kV Contact discharge: ±8Kv

- IEC61000-4-5 (Lightning)1.5A (8/20µs)

RoHS compliant

Dimensions and Pin Configuration



Mechanical Characteristics

Package: DFN1006-2 (1.0×0.6×0.5mm)

Case Material: "Green" Molding Compound.

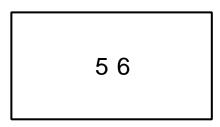
• Moisture Sensitivity: Level 1 per J-STD-020

Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals
- Audio Players
- Keypads, Side Keys, LCD Displays

Marking Information



56 = Device Marking Code

Ordering Information

Part Number	Shipping	Reel Size
PESDU0561P1L	10000/Tape & Reel	7 inch



Absolute Maximum Ratings (TA=25°C unless otherwise specified)

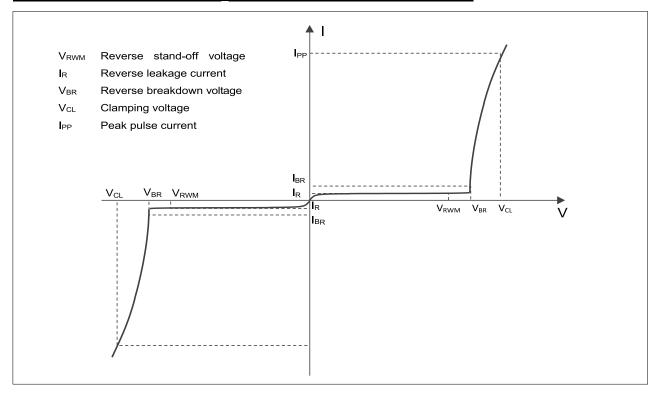
Parameter	Symbol	Value	Unit	
Peak Pulse power(8/20µs)	P _{PK}	20	W	
Peak Pulse Current (8/20µs)	Ірр	1.5	А	
ESD per IEC 61000-4-2 (Air)	V	±15	kV	
ESD per IEC 61000-4-2 (Contact)	V _{ESD}	±8		
Lead temperature	TL	260	°C	
Operating Temperature Range	Тор	-40 ~ + 85	°C	
Storage Temperature Range	Тѕтс	−55 ~ + 150	°C	

Electrical Characteristics (TA=25°C unless otherwise specified)

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}		5		V	
Breakdown Voltage	V_{BR}	5.3	6		V	$I_T = 1mA$
Reverse Leakage Current	I _R			1.0	μA	V _{RWM} = 5V
Clamping Voltage	Vc			13.5	V	I _{PP} = 1.5A (8/20μs pulse)
Junction Capacitance	CJ		2.5		pF	V _R = 0V, f = 1MHz



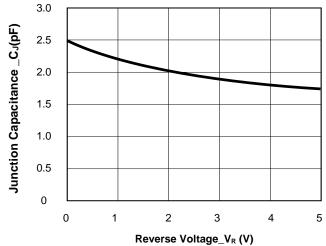
Electrical characteristics (TA = 25°C, unless otherwise noted)

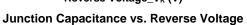


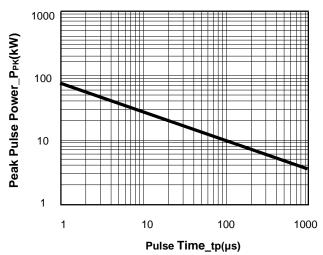
Definitions of electrical characteristics



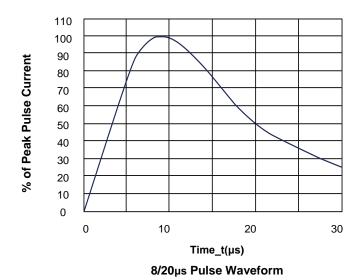
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)

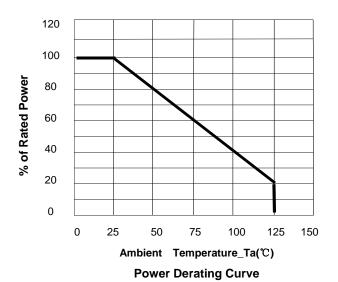






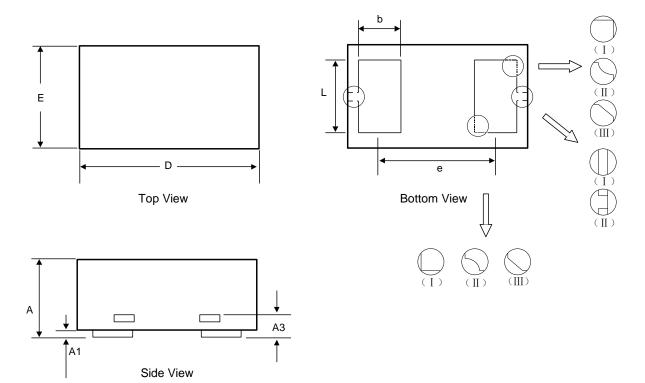
Peak Pulse Power vs. Pulse Time





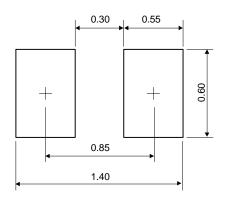


DFN1006-2 Package Outline Drawing



Symbol		Dimensions in Millimeters			
	Min.	Тур.	Max.		
А	0.340	0.450	0.550		
A1	0.000	0.020	0.050		
A3		0.125 Ref.			
D	0.950	1.000	1.075		
E	0.490	0.600	0.675		
b	0.200	0.250	0.300		
L	0.450	0.500	0.550		
e		0.650 BSC			

Recommended PCB Layout (Unit: mm)



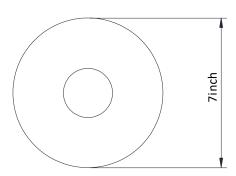
Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

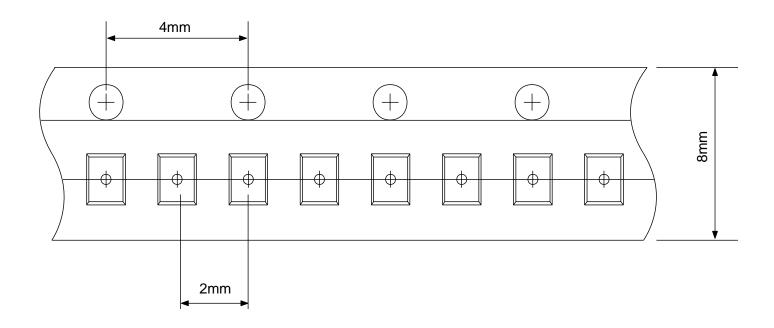


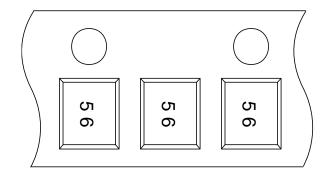
TAPE AND REEL INFORMATION





Tape Dimensions







User Direction of Feed



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